UNIVERSITY OF CENTRAL FLORIDA

Procurement Services
3544 Perseus Loop #160975
Orlando, FL 32816

ADDENDUM

IMPORTANT DOCUMENT – INVITATION TO NEGOTIATE

ITN NUMBER: 2025-02OC

ITN TITLE: Advanced Oxide Etch Tool

OPENING DATE & TIME: August 28, 2025; 2:00 PM

ADDENDUM NUMBER: I ADDENDUM DATE: August 20, 2025

The purpose of this addendum is to answer questions asked during the q/a period.

PLEASE ACKNOWLEDGE RECEIPT OF THIS ADDENDUM AND RETURN IT WITH YOUR OFFER. FAILURE TO SIGN AND RETURN WITH YOUR OFFER COULD RESULT IN REJECTION OF YOUR OFFER.

_____ _____

PROPOSERS SIGNATURE PRINT OR TYPE PROPOSER'S NAME

_____ _____

COMPANY NAME EMAIL ADDRESS

1. Vendor Question: In reference to page 13, specification 9. The system must have a minimum of 8 gas lines for O_2, CHF_3, C4F8, Ar, CF_4, SF_6, N2 with high-precision Mass Flow Controllers (MFCs).

   They appear to be 7 gases instead of 8. Do you mean 6 process gases that are O_2, CHF_3, C4F8, Ar, CF_4, SF_6? And then N2 as venting gas. Also the gas pod can accommodate 8 process gases but only the 6 above would be included. 2 additional process gases could be added later on in the field if necessary. Please let us know if that is our understanding.

   UCF Answer: Your understanding is correct. The configuration should consist of the listed six process gases (O_2, CHF_3, C_4F_8, Ar, CF_4, and SF_6) with N_2 designated for venting. It is acceptable to add two additional gases in the field at a later date if needed.

2. Vendor Question: What is the feature size and etching depth of the sample?

   UCF Answer: Typical feature sizes are 1 µm with an etch depth of 200 nm to 10 µm.

3. Vendor Question: What is the typical edge exclusion considered on the wafer?

   UCF Answer: Typical edge exclusion is 3 – 5 mm.